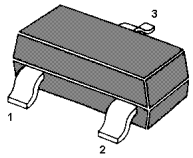
MMBTA13

NPN Silicon Epitaxial Planar Darlington Transistor



1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CES}	30	V
Emitter Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	-55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at V_{CE} = 5 V, I_C =10 mA at V_{CE} = 5 V, I_C =100 mA	 h_{FE} h_{FE}	 5,000 10,000	 - -	 - -
Collector Base Cutoff Current at V_{CB} = 30 V	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at V_{EB} = 10 V	I_{EBO}	-	100	nA
Collector Emitter Breakdown Voltage at I_C = 100 µA	$V_{(BR)CES}$	30	-	V
Collector Emitter Saturation Voltage at I_C = 100 mA, I_B = 0.1 mA	$V_{CE(sat)}$	-	1.5	V
Base Emitter On Voltage at I_C = 100 mA, V_{CE} = 5 V	$V_{BE(on)}$	-	2	V
Transition Frequency at V_{CE} =10 V, I_C =10 mA, f = 100 MHz	f_T	125	-	MHz